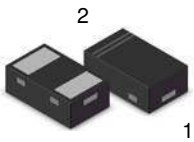
LESD8H6.3T5G
Transient Voltage Suppressors

LESD8H6.3T5G



SOD882

Discription

The ESD8H is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

Specification Features:

- Capacitance 230 pF
- Low Clamping Voltage
- Small Body Outline Dimensions:
  0.039″ x 0.024″ (1.00 mm x 0.60 mm)
- Low Body Height: 0.020″ (0.5 mm)
- Stand−off Voltage: 6.3 V
- Low Leakage
- Response Time is Typically < 1.0 ns
- IEC61000−4−2 Level 4 ESD Protection
- This is a Pb−Free Device

QUALIFIED MAX REFLOW TEMPERATURE: 260°C
Device Meets MSL 1 Requirements

Ordering information

Device	Marking	Shipping
LESD8H6.3T5G	8H	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000−4−2 (ESD) Contact Air		±30 ±30	kV
Total Power Dissipation on FR−5 Board (Note 1) @ T_A = 25°C	P_D	200	mW
Storage Temperature Range	T_{stg}	−55 to +150	°C
Junction Temperature Range	T_J	−55 to +125	°C
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	°C

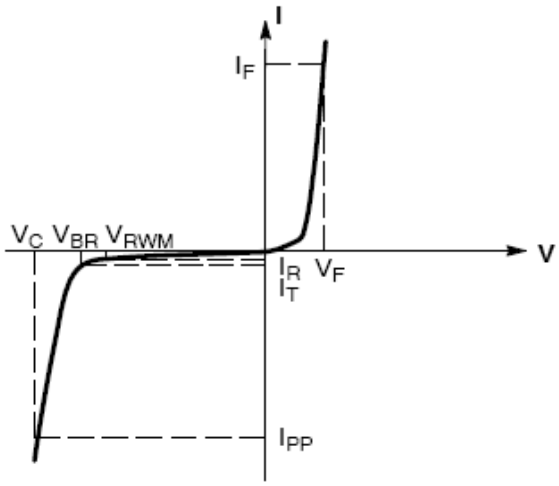
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−5 = 1.0 x 0.75 x 0.62 in.

LESD8H6.3T5G

ELECTRICAL CHARACTERISTICS
(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
P_{pk}	Peak Power Dissipation
C	Capacitance @ V_R = 0 and f = 1.0 MHz



Uni-Directional TVS

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Device	Device Marking	V_{RWM} (V)	I_R (uA) @ V_{RWM}	V_{BR} (V) @ I_T = 1mA (Note 1)		V_C (V) @ I_{PP} =20A	I_{PP} (A) t_p=8/20μs	V_F @ I_F =10mA (V)	C (pF)	$R_{(dynamic)}$(Ω) t_P =2/100μs (TLP)
		Max	Max	Min	Max	MAX	Max	Max	MAX	Typ
LESD8H6.3T5G	8H	6.3	1	7	9.5	11	21	1.1	230	0.11

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

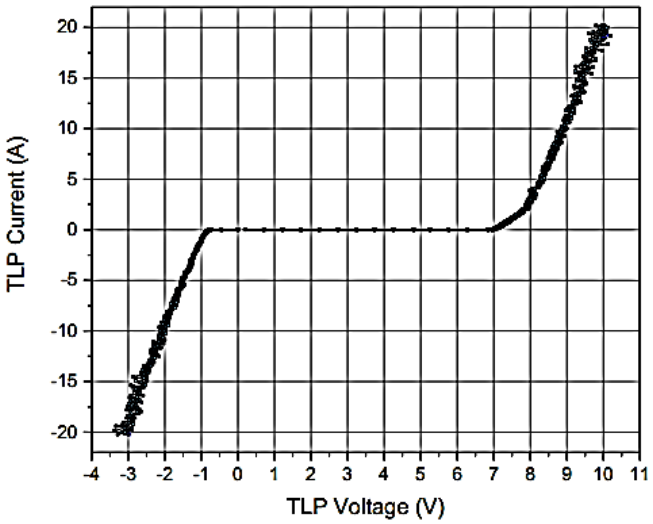


Figure 1 .TLP Measuresent

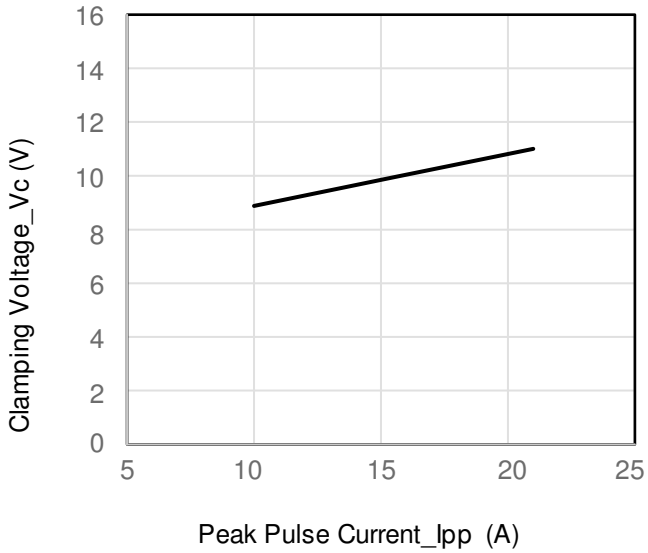


Figure 2 .Clamping Voltage vs.Peak Pulse Current

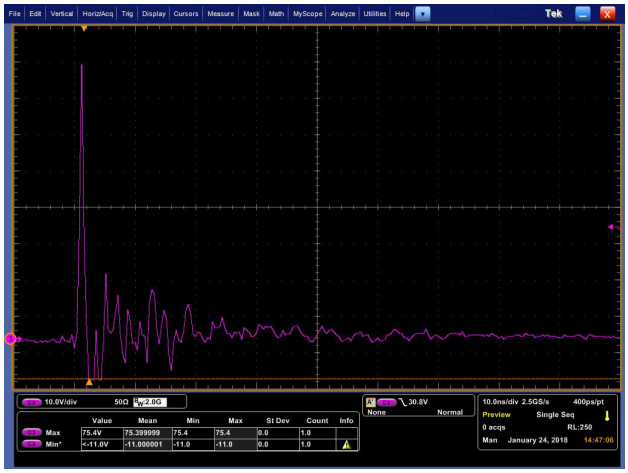


Figure 3.ESD Elamping Voltage Screenshot
Positive 8 kV Eontact per IEE61000-4-2

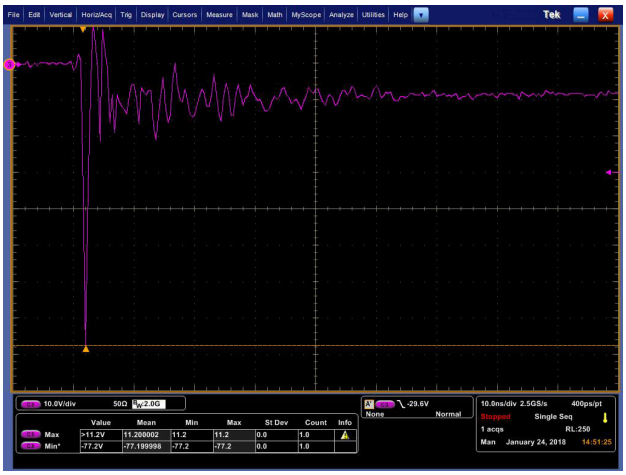
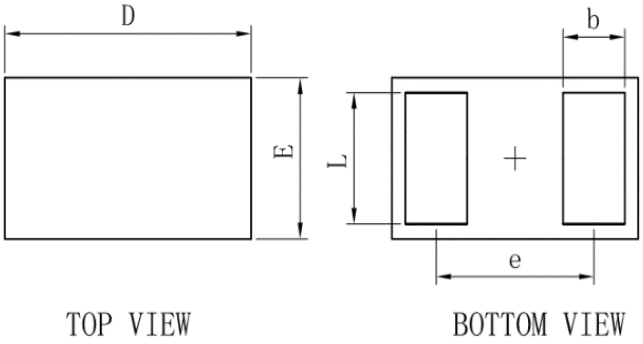
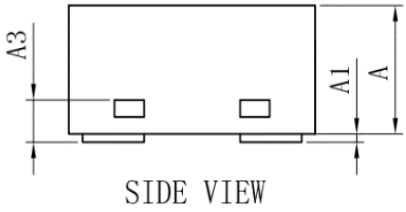


Figure 4.ESD Elamping Voltage Screenshot
Negative 8 kV Eontact per IEE61000-4-2

LESD8H6.3T5G

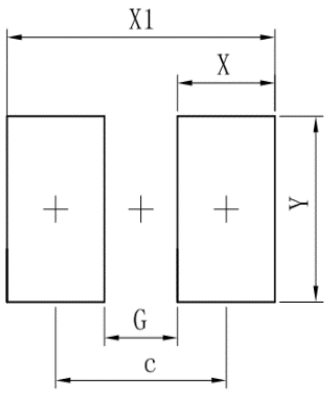
OUTLINE AND DIMENSIONS





SOD882			
Dim	Min	Typ.	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			

SOLDERING FOOTPRINT



Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70

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